# **General Purpose Transistors**

# **PNP Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

| Rating                         | Symbol         | Value | Unit |
|--------------------------------|----------------|-------|------|
| Collector – Emitter Voltage    | $V_{CEO}$      | -45   | V    |
| Collector – Base Voltage       | $V_{CBO}$      | -50   | V    |
| Emitter – Base Voltage         | $V_{EBO}$      | -5.0  | V    |
| Collector Current – Continuous | I <sub>C</sub> | -500  | mAdc |

# THERMAL CHARACTERISTICS

| Characteristic   | Symbol                            | Max         | Unit        |
|--|-----------------------------------|-------------|-------------|
| Total Device Dissipation FR-5 Board,<br>(Note 1) T <sub>A</sub> = 25°C<br>Derate above 25°C  | P <sub>D</sub>                    | 225<br>1.8  | mW<br>mW/°C |
| Thermal Resistance, Junction–to–Ambient (Note 1)   | $R_{\theta JA}$                   | 436         | °C/W        |
| Total Device Dissipation Alumina Substrate, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C | P <sub>D</sub>                    | 300<br>2.4  | mW<br>mW/°C |
| Thermal Resistance, Junction–to–Ambient (Note 2)   | $R_{\theta JA}$                   | 417         | °C/W        |
| Junction and Storage Temperature   | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C          |

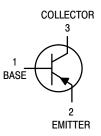
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 Board, 1 oz. Cu, 100mm<sup>2</sup>.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

#### **MARKING DIAGRAM**



5xx = Device Code xx = A1, B1, or C $M = Date Code^*$ 

= Pb–Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted.)

| Symbol                | Min  | Тур   | Max  | Unit                 |
|-----------------------|--|---|--|----------------------|
|                       |  |   |  |                      |
| V <sub>(BR)</sub> CEO | -45  | _   | _  | V                    |
| V <sub>(BR)</sub> CES | -50  | -   | -  | V                    |
| V <sub>(BR)EBO</sub>  | -5.0   | _   | _  | V                    |
| Ісво                  | _<br>_   | -<br>-  | -100<br>-5.0   | nA<br>μA             |
|                       |  |   |  |                      |
| SBC807-25L            | 100<br>160<br>250<br>40  | -<br>-<br>-                                     | 250<br>400<br>600<br>–   | -                    |
| V <sub>CE(sat)</sub>  | -  | -   | -0.7   | V                    |
| V <sub>BE(on)</sub>   | -  | -   | -1.2   | V                    |
|                       | •  | •   | =  |                      |
| f⊤                    | 100  | -   | _  | MHz                  |
| C <sub>obo</sub>      | -  | 10  | -  | pF                   |
|                       | V(BR)CEO  V(BR)CES  V(BR)EBO  ICBO  ICBO  NFE  VCE(sat)  VBE(on) | V(BR)CEO -45  V(BR)CES -50  V(BR)EBO -5.0  ICBO | V(BR)CEO -45 -  V(BR)CES -50 -  V(BR)EBO -5.0 -  ICBO  ICBO  SBC807-25L SBC807-40L 250 -  VCE(sat)  VBE(on)  T 100 -  T 100 - | V <sub>(BR)CEO</sub> |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **ORDERING INFORMATION**

| Device         | Specific Marking | Package             | Shipping <sup>†</sup> |  |
|----------------|------------------|---------------------|-----------------------|--|
| BC807-16LT1G   | 504              |                     | 3000 / Tape & Reel    |  |
| SBC807-16LT1G* | 5A1              |                     |                       |  |
| BC807-16LT3G   | E A 4            | SOT-23<br>(Pb-Free) | 10.000 / Topo % Dool  |  |
| SBC807-16LT3G* | 5A1              |                     | 10,000 / Tape & Reel  |  |
| BC807-25LT1G   | 5B1              |                     | 2000 / Tara & Basi    |  |
| SBC807-25LT1G* |                  |                     | 3000 / Tape & Reel    |  |
| BC807-25LT3G   | 5B1              |                     | 10,000 / Tape & Reel  |  |
| SBC807-25LT3G* | 361              |                     | 10,000 / Tape & Reel  |  |
| BC807-40LT1G   | 5C               |                     | 2000 / Tono % Dool    |  |
| SBC807-40LT1G* | 50               |                     | 3000 / Tape & Reel    |  |
| BC807-40LT3G   | 5C               |                     | 10.000 / Topo % Book  |  |
| SBC807-40LT3G* | 50               |                     | 10,000 / Tape & Reel  |  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
\*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

#### **TYPICAL CHARACTERISTICS - BC807-16LT1**

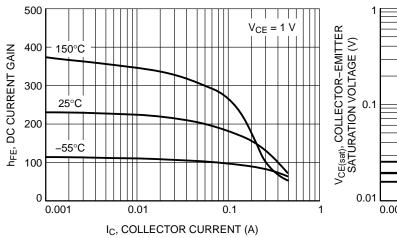


Figure 1. DC Current Gain vs. Collector Current

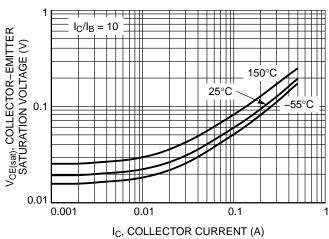


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

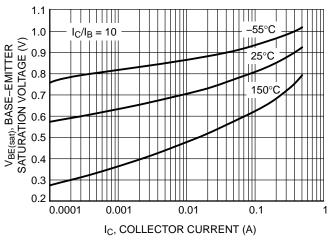


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

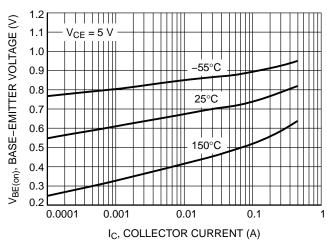


Figure 4. Base Emitter Voltage vs. Collector Current

# **TYPICAL CHARACTERISTICS - BC807-16LT1**

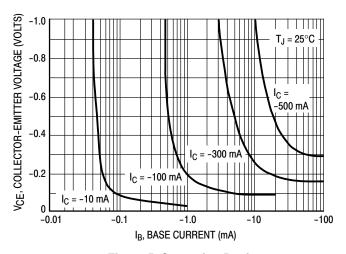
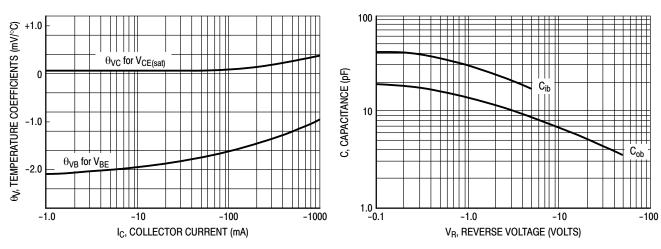


Figure 5. Saturation Region



**Figure 6. Temperature Coefficients** 

Figure 7. Capacitances

#### **TYPICAL CHARACTERISTICS - BC807-25LT1**

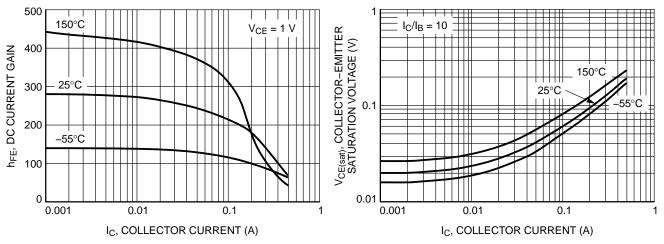


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

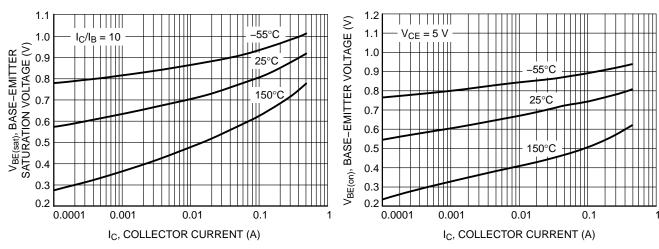


Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

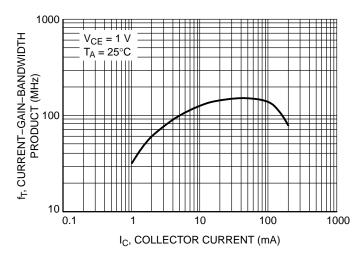


Figure 12. Current Gain Bandwidth Product vs. Collector Current

# **TYPICAL CHARACTERISTICS - BC807-25LT1**

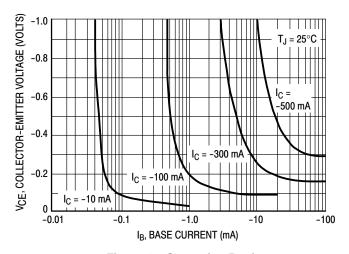


Figure 13. Saturation Region

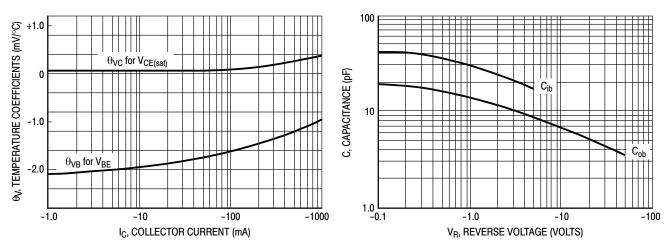


Figure 14. Temperature Coefficients

Figure 15. Capacitances

#### TYPICAL CHARACTERISTICS - BC807-40LT1

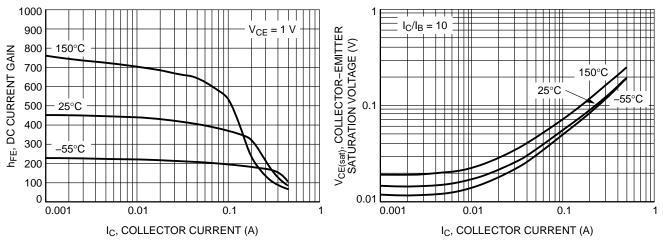


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

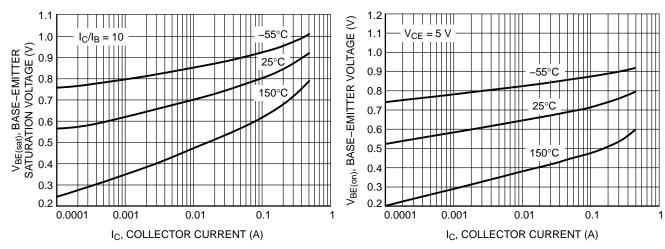


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

Figure 19. Base Emitter Voltage vs. Collector
Current

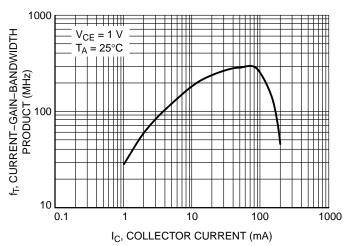


Figure 20. Current Gain Bandwidth Product vs. Collector Current

# **TYPICAL CHARACTERISTICS - BC807-40LT1**

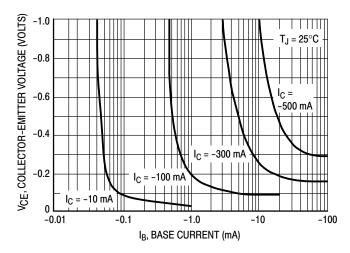


Figure 21. Saturation Region

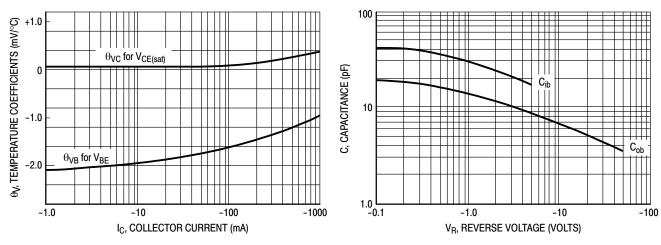


Figure 22. Temperature Coefficients

Figure 23. Capacitances

# TYPICAL CHARACTERISTICS - BC807-16LT1, BC807-25LT1, BC807-40LT1

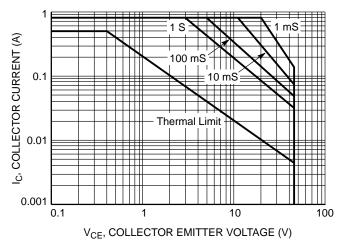


Figure 24. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

0.017

0.021

0.094

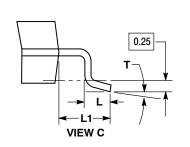
0.022

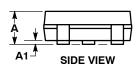
0.027

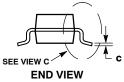
0.104

10°

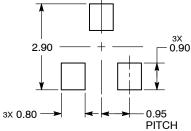
# SCALE 4:1 D Ε – 3X h **TOP VIEW**







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

PIN 1. RETURN

3. INPUT

3. ANODE

STYLE 28: PIN 1. ANODE 2. ANODE

2. OUTPUT

#### NOTES:

0.43

0.54

2.40

0.30

0.35

2.10

0°

ΗE

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

|     | MILLIMETERS |      |      |       | INCHES |       |
|-----|-------------|------|------|-------|--------|-------|
| DIM | MIN         | NOM  | MAX  | MIN   | NOM    | MAX   |
| Α   | 0.89        | 1.00 | 1.11 | 0.035 | 0.039  | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.000 | 0.002  | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015 | 0.017  | 0.020 |
| С   | 0.08        | 0.14 | 0.20 | 0.003 | 0.006  | 0.008 |
| D   | 2.80        | 2.90 | 3.04 | 0.110 | 0.114  | 0.120 |
| Е   | 1.20        | 1.30 | 1.40 | 0.047 | 0.051  | 0.055 |
| 9   | 1 78        | 1 90 | 2 04 | 0.070 | 0.075  | 0.080 |

0.55

0.69

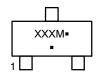
2.64

#### 10° 0° **GENERIC MARKING DIAGRAM\***

0.012

0.014

0.083



XXX = Specific Device Code

= Date Code

PIN 1. ANODE 2. CATHODE

3. GATE

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

| STYLE 1 THRU 5:<br>CANCELLED | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE | N                |                |
|------------------------------|---|---|--|------------------|----------------|
| STYLE 9:                     | STYLE 10:   | STYLE 11:   | STYLE 12:  | STYLE 13:        | STYLE 14:      |
| PIN 1. ANODE                 | PIN 1. DRAIN  | PIN 1. ANODE  | PIN 1. CATHODE   | PIN 1. SOURCE    | PIN 1. CATHODE |
| 2. ANODE                     | 2. SOURCE   | 2. CATHODE  | 2. CATHODE   | 2. DRAIN         | 2. GATE        |
| 3. CATHODE                   | 3. GATE   | 3. CATHODE-ANODE                                      | 3. ANODE   | 3. GATE          | 3. ANODE       |
| STYLE 15:                    | STYLE 16:   | STYLE 17:   | STYLE 18:  | STYLE 19:        | STYLE 20:      |
| PIN 1. GATE                  | PIN 1. ANODE  | PIN 1. NO CONNECTION                                  | PIN 1. NO CONNECTION                                       | N PIN 1. CATHODE | PIN 1. CATHODE |
| 2. CATHODE                   | 2. CATHODE  | 2. ANODE  | 2. CATHODE   | 2. ANODE         | 2. ANODE       |
| 3. ANODE                     | 3. CATHODE  | 3. CATHODE  | 3. ANODE   | 3. CATHODE-ANODE | 3. GATE        |
| STYLE 21:                    | STYLE 22:   | STYLE 23:   | STYLE 24:  | STYLE 25:        | STYLE 26:      |

PIN 1. ANODE

ANODE

CATHODE

| DOCUMENT NUMBER: | 98ASB42226B     | Electronic versions are uncontrolled except when accessed directly from the Document Reposit<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |             |
|------------------|-----------------|---|-------------|
| DESCRIPTION:     | SOT-23 (TO-236) |   | PAGE 1 OF 1 |

PIN 1. GATE 2. DRAIN

3. SOURCE

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PIN 1. GATE

2. SOURCE

3. CATHODE

DRAIN

STYLE 27: PIN 1. CATHODE 2. CATHODE

PIN 1. CATHODE 2. ANODE

3. NO CONNECTION

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